



DB: USPAT US-PG-PUB EPO JPO DER-ENT IBM TDB

Deletions: 08

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### 33 and multilayer

10/27/04 TDW

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NUM

L Number	Hits	Search Text	DB	Time stamp
1	9	"6061228"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:33
2	3	"6351880"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:25
3	2613025	via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:40
4	535	embedded near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:41
5	282	via\$1 and ( embedded near capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:42
6	191	(via\$1 and ( embedded near capacitor)) and fill\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:42
7	14	((via\$1 and ( embedded near capacitor)) and fill\$5) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:45
8	20446	bore adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:46
9	2	(bore adj hole) near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:47
10	68	on adj chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:47
11	26371	on-chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:48
12	298	on-chip near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:48

13	26	(on-chip near capacitor) and hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:49
14	0	(on-chip near capacitor) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 11:49
15	150	(on-chip near capacitor) and via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:19
16	7	capacitor adj using adj via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:22
17	594042	capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:23
18	17737	via\$1 near capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:24
19	15109	via\$1 adj capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:24
20	443	(via\$1 adj capacitor\$1) and embedded	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:25
21	70	((via\$1 adj capacitor\$1) and embedded) and IC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:40
22	172	((via\$1 adj capacitor\$1) and embedded) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:26
23	13501	via\$1 adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:40
24	23	( embedded near capacitor) and (via\$1 adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:11

25	2153	metallic near via\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:36
27	313	(metallic near via\$1) and capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:13
28	164	((metallic near via\$1) and capacitor\$1) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:13
29	0	capacitor adj formed adj from adj via\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:29
30	7	(metallic near via\$1) and capacitor and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:29
31	0	metallic near via\$1 near capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:37
32	105605	361/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:38
33	493	(via\$1 adj capacitor) and 361/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:38
34	5	((via\$1 adj capacitor) and 361/\$.ccls.) and LTCC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:42
35	34	((via\$1 adj capacitor) and 361/\$.ccls.) and multilayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:42